

Hollow-Cathode Plasma-Assisted ALD of CuO Thin Films: Evaluating Self-Limiting Growth Conditions and Material Properties

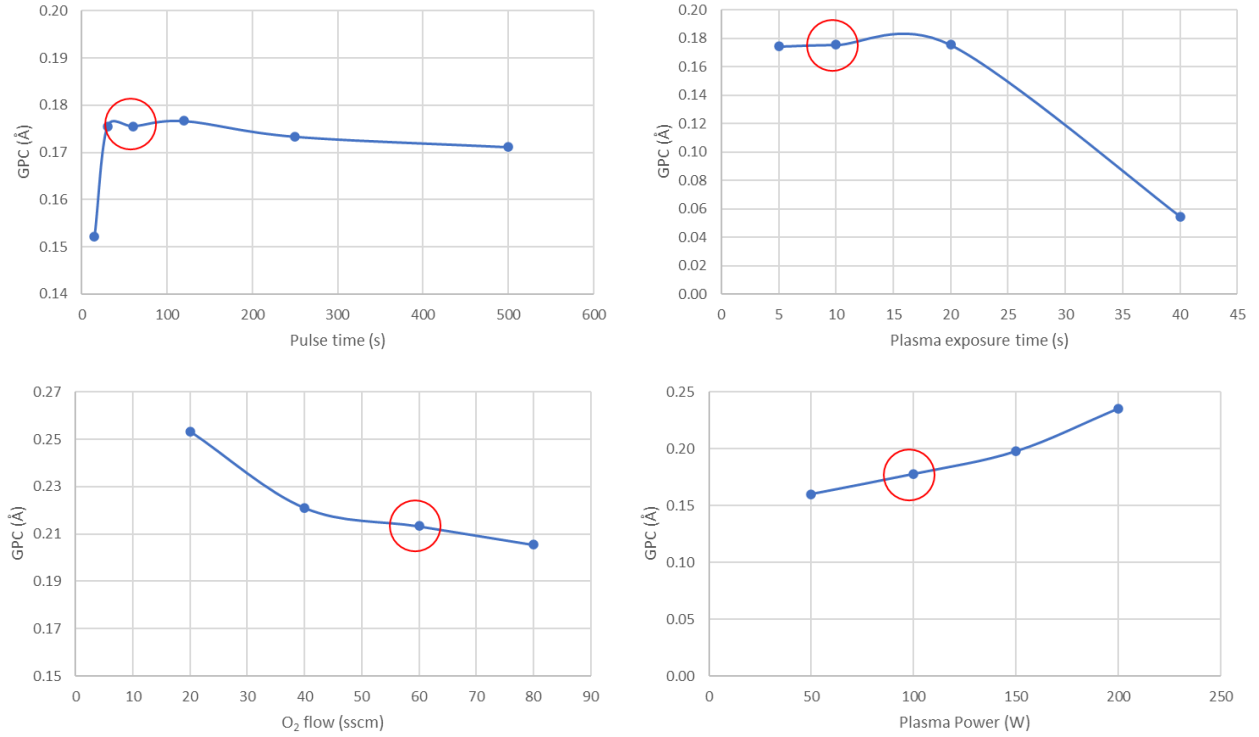


Figure 1. CuO saturation study monitored via in-situ MWE. The GPC values were recorded in relation to (a) precursor pulse time at 100W, 200°C; (b) plasma exposure time at 100W, 200°C; (c) oxygen flow rate at 100W, 200°C and (d) plasma power at 200°C.

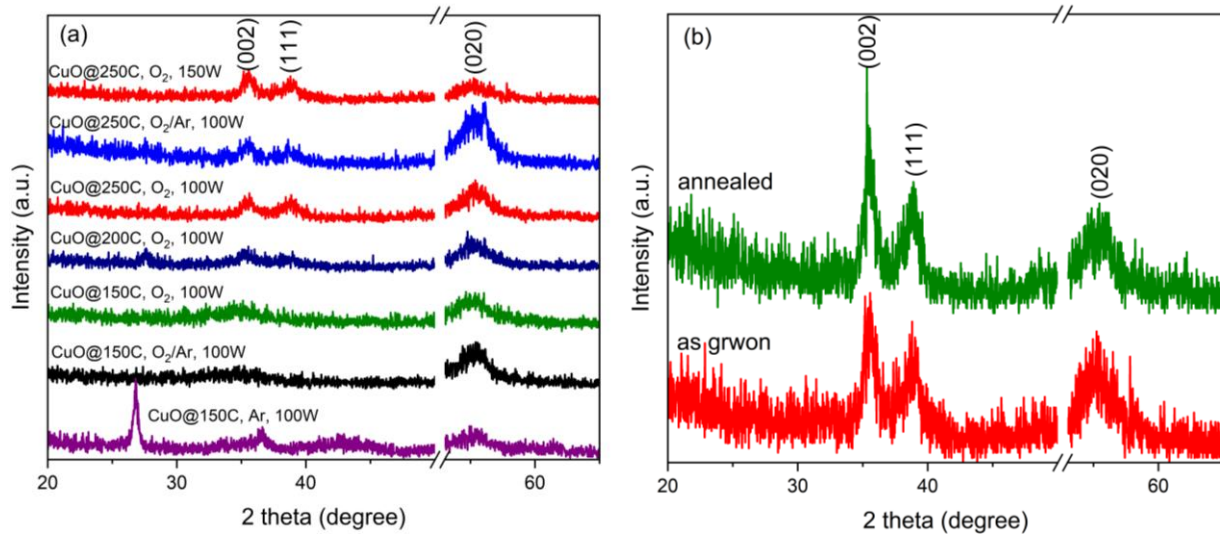


Figure 2. GIXRD patterns of CuO films: (a) deposited under various temperatures and plasma conditions, (b) film grown at 250 °C under O₂ flow with 150 W plasma power, before and after annealing.